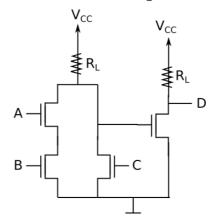
## **CSU0007 Basic Electronics, Homework 4**

- Three questions in total. Submit your work via Moodle before 9PM, Dec 4th, 2020.
- Clearly state your reasoning to earn full score.
- Textbook coverage: Section 6.1 to Section 6.8 (before Section 6.8.1).
- The assignment for self-study: Section 6.8.1 in the textbook (no need to submit this assignment).
- 1. (30 points) Consider the S model. In the following circuit, suppose the input {A, B, C} corresponds to logical {0, 1, 0}. What would be the logical value output at D?



- 2. (40 points) Now, consider the SR model. Explain in your own words that under the static discipline,
  - 1. (20 points) why we must have  $V_{IL} < V_{T}$  ?
  - 2. (20 points) why we must have  $V_{OL} > V_{CC} \frac{R_{ON}}{R_{ON} + R_I}$  ?
- 3. (30 points) Consider the SR model and the following specification: The noise margin is 0.5V for logical 0 and 1V for logical 1. The forbidden region is from 1V to 1.5V.  $V_T$ =1.2V,  $V_{cc}$ =3.3V, and  $R_N$ =5k $\Omega$ . Now, to build a MOSFET to meet this specification, what would be the maximum feasible value of ratio  $\frac{L}{W}$ ? Assuming that  $R_L$ =8k $\Omega$ .